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Silicon NPN Power Transistors

2N5664 2N5665

DESCRIPTION

- With TO-66 package
- High breakdown voltage

APPLICATIONS

- High speed switching and linear amplifier
- High-voltage operational amplifiers
- Switching regulators ,converters
- Deflection stages and high fidelity amplifers

Fig.1 simplified outline (TO-66) and symbol

PINNING (See Fig.2)

PIN	DESCRIPTION
1	Base
2	Emitter
3	Collector

Absolute maximum ratings(Ta=25℃)

SYMBOL	PARAMETER		CONDITIONS	VALUE	UNIT
V_{CBO}	Collector-base voltage	2N5664	Open emitter	250	V
		2N5665		400	
V_{CEO}	Collector-emitter voltage	2N5664	Open base	200	V
		2N5665		300	
V_{EBO}	Emitter-base voltage		Open collector	6	V
I_C	Collector current			5.0	A
I_B	Base current			1.0	A
P_T	Total power dissipation		T_C=25℃	52.5	W
T_j	Junction temperature			200	℃
T_{stg}	Storage temperature			-65~200	℃

THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	MAX	UNIT
$R_{th\ j\text{-}C}$	Thermal resistance junction to case	5.0	℃/W

Quality Semi-Conductors